Octal Bus Buffer

The MC74VHCT541A is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT541A is a noninverting, 3–state, buffer/line driver/line receiver. When either $\overline{OE1}$ or $\overline{OE2}$ is high, the terminal outputs are in the high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT541A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage—input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 5.4 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.6 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- Pb-Free Packages are Available*

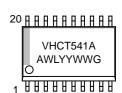


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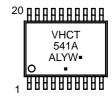
MARKING DIAGRAMS







TSSOP-20 SUFFIX DT CASE 948E







A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = = Pb-Free Package
(Note: Microdot may be in either location)

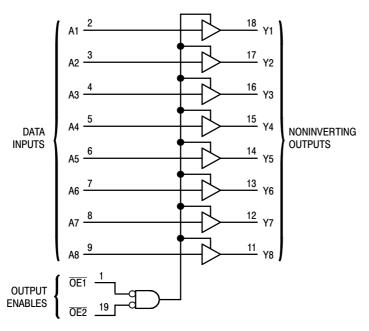
FUNCTION TABLE

	Inputs	Output Y	
OE1	OE2	Α	Output 1
L	L	L	L
L	L	Н	Н
Н	X	Х	Z
Х	Н	Χ	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



_			
OE1	1●	20	□ v _{cc}
A1 [2	19	OE2
A2 [3	18] Y1
A3 [4	17] Y2
A4 [5	16] Y3
A5 [6	15] Y4
A6 [7	14] Y5
A7 [8	13] Y6
A8 🛘	9	12] Y7
GND [10	11] Y8

Figure 2. Pin Assignment

Figure 1. Logic Diagram

MAXIMUM RATINGS

	(062			
	Figure 1. Logic Diagram		a sã	君
MAXIMU	M RATINGS	逐为春	W.	CI
Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V	
V _{in}	DC Input Voltage	-0.5 to + 7.0	V	
V _{out}	DC Output Voltage Outputs in 3-State High or Low State	- 0.5 to + 7.0 - 0.5 to V _{CC} + 0.5	V	
I _{IK}	Input Diode Current	- 20	mA	
I _{OK}	Output Diode Current (V _{OUT} < GND; V _{OUT} > V _{CC})	± 20	mA	
I _{out}	DC Output Current, per Pin	± 25	mA	
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA	
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW	
T _{stg}	Storage Temperature	- 65 to + 150	°C	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

SOIC Packages: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage Outputs in 3-State High or Low State	0	5.5 V _{CC}	V
T _A	Operating Temperature	- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time V_{CC} =5.0V ± 0.5 V	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	1	T _A = 25	°C	T _A = - 40	0 to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V _{OH}	V _{OH} Minimum High–Level Output Voltage V _{in} = V _{IH} or V _{IL}	$I_{OH} = -50 \mu A$	4.5	4.4	4.5		4.4		V
		I _{OH} = - 8mA	4.5	3.94			3.80		
V _{OL}	Maximum Low-Level Output	I _{OL} = 50μA	4.5		0.0	0.1		0.1	V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OL} = 8mA	4.5			0.36		0.44	
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
I _{OZ}	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μΑ
I _{CCT}	Quiescent Supply Current	Per Input: V _{IN} = 3.4V Other Input: V _{CC} or GND	5.5			1.35		1.50	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0			0.5		5.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$)

		. 4	J. 100	$\Gamma_{A} = 25$	°C	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to Y	V_{CC} = 5.0 ± 0.5V C_L = 15pF C_L = 50pF	U.	5.0 5.5	6.9 7.9	1.0 1.0	8.0 9.0	ns
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	$\begin{array}{ccc} V_{CC} = 5.0 \pm 0.5 V & C_L = 15 pF \\ R_L = 1 k \Omega & C_L = 50 pF \end{array}$		8.3 8.8	11.3 12.3	1.0 1.0	13.0 14.0	ns
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Y	$\begin{aligned} V_{CC} &= 5.0 \pm 0.5 V & C_L &= 50 pF \\ R_L &= 1 k \Omega \end{aligned}$		9.4	11.9	1.0	13.5	ns
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 5.0 \pm 0.5 V$ $C_L = 50 pF$ (Note 1)			1.0		1.0	ns
C _{in}	Maximum Input Capacitance			4	10		10	pF
C _{out}	Maximum 3–State Output Capacitance (Output in High Impedance State)			9				pF

Ī			Typical @ 25°C, V _{CC} = 5.0V	
	C_{PD}	Power Dissipation Capacitance (Note 2)	19	pF

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 ns$, $C_L = 50 pF$, $V_{CC} = 5.0 V$)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	1.2	1.6	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-1.2	-1.6	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/8$ (per bit). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT541ADW	SOIC-20WB	38 Units / Rail
MC74VHCT541ADWG	SOIC-20WB (Pb-Free)	38 Units / Rail
MC74VHCT541ADWR2	SOIC-20WB	1000 / Tape & Reel
MC74VHCT541ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT541ADT	TSSOP-20*	75 Units / Rail
MC74VHCT541ADTG	TSSOP-20*	75 Units / Rail
MC74VHCT541ADTR2	TSSOP-20*	2500 / Tape & Reel
MC74VHCT541ADTRG	TSSOP-20*	2500 / Tape & Reel
MC74VHCT541AMEL	SOEIAJ-20	2000 / Tape & Reel
MC74VHCT541AMELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

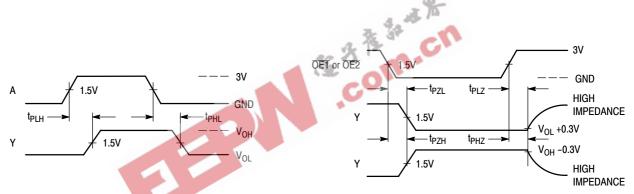
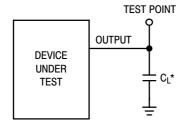


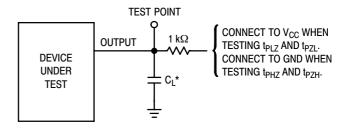
Figure 3. Switching Waveform

Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit

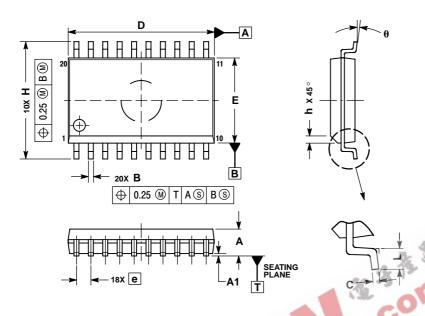


*Includes all probe and jig capacitance

Figure 6. Test Circuit

PACKAGE DIMENSIONS

SOIC-20 WB **DW SUFFIX** CASE 751D-05 ISSUE G



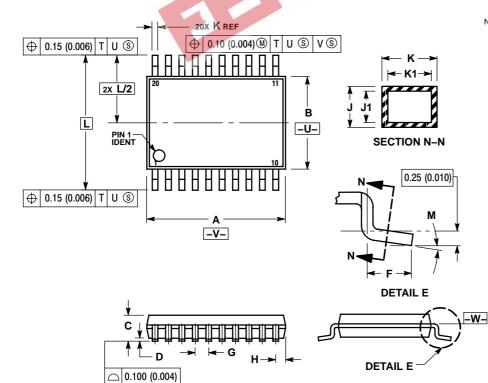
NOTES:

- NOTES:

 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10 0.25			
В	0.35 0.49			
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
e	1.27	BSC		
H.	10.05	10.55		
h	0.25	0.75		
Ĺ	0.50	0.90		
θ	0 °	7 °		
_				

TSSOP-20 **D5 SUFFIX** CASE 948E-02 ISSUE B



-T- SEATING

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE

 - MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

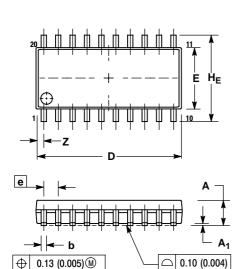
 JUMENSION B DOES NOT INCLUDE
 - INTERLEAD FLASH OR PROTRUSION INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 - DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 5. TERMINAL NUMBERS ARE SHOWN

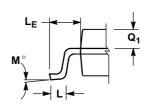
 - 6. TERMINAL NUMBERS ARE GIGO.
 FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007 0.010		
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

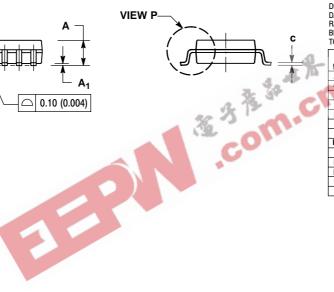
PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE A**





DETAIL P



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	-	2.05	i	0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.15	0.25	0.006	0.010	
D	12.35	12.80	0.486	0.504	
E	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050	BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10 °	0°	10°	
Q_1	0.70	0.90	0.028	0.035	
Z		0.81		0.032	

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